## ELECTRONICS ENGINEERING

1. Just as a voltage amplifier signal voltage a power amplifier.
1.amplifier power
2.amplifier signal
3.converts the signal ac power into DC power
4.converts a dc power into useful AC power
2. Cross over distortion in class - B push-p amplifiers:
3. Is due to transistor operating near saturation region
4. Can be eliminated by operating them in class operation
5. Occurs because two power transistors do not exactly matching parameters
6. Always occurs in low signal area
7. If the load p.f. is 0.866 , then the average p.f. the $v-b a n k$ is
8. 0.886
9. 0.75
3.0.51
10. 0.65
4.AT-T connection has higher ratio of utiliza ${ }^{x}$ that $n$ a $V-V$ connection only when
11. Identical transformers are used
12. Load power factor is leading
13. Load power factor is unity
14. Non-identical transformers are used
15. A commercial power supply has a voltage regulation of:
16. 1\%
2.5\%
3.20\%
4.50\%
17. Which stage is of a d.c. power supply uses zener diode
18. Rectifier
19. Voltage divider
20. Filter
21. Regulator
22. Which rectifier requires 4 diodes ?
23. half wave rectifier
24. full wave rectifier
25. bridge type rectifier
26. Voltage quadrupler
8.The advantage of dynamic RAMs over static RAMs is
27. Lower power consumption
28. Higher power consumption
29. Higher packing density
30. Lower packing density
31. The address range for $M=64$ words storage in hexadecimal format is
32. 00 to 3 F
33. 00 to FF
34. 0 to 3
35. 0 to F
36. The 8085 is a - microprocessor
37. 4 bit
38. 8 bit
39. 16 bit
40. 32 bit
41. The voltage gain of a common base amplifier depends on
42. Load resistor RL
43. input resistance of transistor
44. Ac alpha
45. All the above
46. A JFET has the disadvantage of
47. Having low input impedance
48. Having high output impedance
49. Having small gain band-width product
50. Possessing positive temperature coefficient
51. A FET is preferred over an ordinary transistor because it
52. Permits high degree of isolation between input \& output circuits
53. Has low noise level
54. Has very high power gain
55. Has all the above properties
56. To turn a UJT ON, the forward bias on emitter diode should be:
57. more than the peak point voltage
58. less than the peak point voltage
59. Equal to the peak point voltage
60. Equal to the stand - off voltage
61. Which of the following statements is wrong for transistor biasing methods:
62. The base resistor method does not provide stabilization of operating point 2. The biasing with feedback resistor provides only some stabilization
63. Base resistor method provides better stabilization than collector feedback method
4.Voltage divider bias is widely used because it has stable operating point
64. The disadvantage of voltage divider bias is that
65. it has a high stability factor
66. it has many resistors
67. it allows thermal runaway
68. it does not allow faithful amplification
69. In class-A amplifier conduction extends over $360^{\circ}$ because the operating point.
70. Located near saturation point
71. Located at or near cut-off point
72. Located on load line
73. Located in the centre of load line
74. The capacitance of reverse biased P-N junction
75. Decreases with increasing the reverse bias
76. Increases with increasing the reverse bias
77. Depends only on reverse saturation current
78. Makes the P-N junction more effective at high frequencies
79. In a transistor
80. Emitter is heavily doped while the collector is moderately doped
81. Collector base junction is forward biased
82. Emitter is made wider than collector
83. The input resistance is much higher than output resistance
84. If a transistor were operated with emitter and collector interchanged, then
1 .emitter current will increase
85. Collector current will increase
86. Base current will decrease
87. No current flow will take place
88. When a current flows in a conductor, the order of magnitude of the drift velocity of electrons in it is
89. $\mathrm{IO}^{10} \mathrm{~cm} / \mathrm{s}$
90. $10^{-2} \mathrm{~cm} / \mathrm{s}$
91. $10^{4} \mathrm{~cm} / \mathrm{s}$
92. $10^{-1} \mathrm{~cm} / \mathrm{s}$
93. When an alternating potential is applied to a capacitor, the current in the circuit will
94. lead the applied potential
95. lag the applied potential
96. be in phase with the applied potential
97. none
98. In application of superposition theorem, one is required to solve as many circuits as there are
99. Nodes
100. Branches
101. Meshes
102. Sources
103. Norton's equivalent of a circuit consists of a
104. Constant current generator with parallel impedance
105. Constant current generator in series with an infinite resistance
106. Constant current generator in parallel with high impedance
107. Constant current generator in series with low impedance
25.. We require a resistor of $47 \mathrm{~K} \Omega$ - with $\pm 10 \%$ tolerance. The sequence of colour band on this resistor would be
108. Yellow, violet, orange $\boldsymbol{\&}$ silver
109. Yellow, brown, orange \& silver
110. Yellow, violet, orange \& gold
111. Yellow, violet, brown $\boldsymbol{\&}$ gold
26.. The high level language can be translated into machine language with the help of
112. Assembler
113. Stack pointer
114. Compiler
115. Multiplexer
116. The Intel 8259 is a - chip programmable interrupt controller
117. Single
118. Double
119. Triple
120. All of the above
28.An analog voltage in the range of 0 to V volts into be converted into 3bit digital output. It is divided into eight intervals. The top \& the bottom intervals are V/14 \& the middle six intervals are V/7. The maximum quantization error will be:
121. 0
122. $\frac{V}{7}$
123. $\frac{V}{14}$
124. V
125. Frequency of oscillation of an AMV depends upon
126. RC values of the circuit
127. Collector load resistors
128. Transistor
129. Width of input pulse
130. Multivibrators can be used as:
131. Frequency dividers
132. Memory elements in computers
133. Square wave, saw tooth \& pulse generators
134. All the above
135. The permeability of a diamagnetic material is
136. Zero
137. Less than 1
138. Equal to 1
139. More than 1
140. The potential barrier at a $\mathbf{P}-\mathrm{N}$ junction is due to
141. Majority carriers
142. Minority carriers
143. Both majority and minority carriers
144. Fixed donor and acceptor ions
145. These self inductance of a circuit is defined as twice the work done against the induced e.m.f. on establishing unit current in the coil. If the current to be established in the coil is doubled, the work done against the induced e.m.f. will be
146. Doubled
147. Halved
148. four times
149. Quarter times
150. The drift velocity of free electrons in a conducting wire carrying a current $I$ is $V$. If in a wire of the same metal, but of double the radius, the current be 21 , then the drift velocity of electrons will be
151. V
152. $\frac{V}{2}$
153. $\frac{V}{4}$
154. 4 V
155. A commercial power supply has a voltage regulation of 1. $1 \% \quad 2.5 \% \quad 3.20 \% \quad 4.50 \%$
156. In a bridge rectifier
157. PIV has a value $V_{m}$
158. Centre tap of secondary is not required
159. Smaller transformer can be used
160. All
161. In an R-2R ladder D/A converter, the input resistance is
162. Not same for all digital inputs
163. R for each input
164. 2 R for each input
165. 3R for each input
166. The speed of a D.C. motor can be controlled by varying
167. Its flux per pole
168. Resistance of armature circuit
169. Applied voltage
170. All of the above
171. The chief advantage of Ward-Leonard system D.C. motor speed control is that is
172. Can be used even for small motors
173. has high overall efficiency at all speeds
174. Gives smooth, sensitive and wide speed control
175. Uses a flywheel to reduce fluctuations in power demand
176. A transformer transforms
177. Frequency
178. Voltage
179. Current
180. Voltage and current
181. Which of the following is not a basic element of a transformer ?
182. Core
183. Primary winding
184. Secondary winding
185. Mutual flux
186. The slight curvature at the lower end of the O.C.C. of a self-excited dc generator is due to
187. residual pole flux 2 . high armature speed
3.magnetic inertia 4. high field circuit resistan
188. for the voltage built-up a self-excited D.C. generator, which of the following is not an essential condition.
1.there must be some residual flux
2.field winding mmf must aid the residual flux
3.total field circuit resistance must be less than $t$ critical value
4.armature speed must be very high
44.The Intel 8212 is an - non programmable I/O port
189. 4 - bit 2.8 - bit 3.16 - bit 4.32 - bit
45.. The terms 'soft sectored' and 'hard sectored' are used in connection with

| 1. $\mu \mathrm{P}$ | 2. RAM |
| :--- | :--- |
| 3. ROM | 4. Floppy disk |

46.In temperature monitoring system - transducers are used 1. $2 \quad 2.3 \quad 3.4 \quad 4.6$
47.Today most computers use-technology for their operation

1. Germanium 2. Silicon
2. Gallium - Arsenide 4. Gallium - telluride
48.In a multivibrator
1.feedback between two stages is $100 \%$
2.positive feedback is employed
3.when one transistor is on, the other is off
4.all
49.An OP-AMP can be classified as
1.Linear amplifier
2.Low - Rin amplifier
3.Positive - feedback amplifier
4.RC - coupled amplifier
50.Amplification factor of a circuit is 50. For oscillator is feedback factor should be
$1.50 \quad 2.100 \quad 3 . \frac{1}{50} \quad 4 . \frac{1}{100}$
3. Positive feedback is used in
4. Amplifier 2. Rectifier 3.Oscillator 4. Detector
5. Darlington pair
1.is a three terminal device with very high current gain
2.has a very high input impedance
3.has a very low output
4.all the above are true
53.Which of the following has got a positive susceptibility
1.Diamagnetic
2.Paramagnetic
3.Ferromagnetic
4.both Paramagnetic \& ferromagnetic
6. In a tunnel diode, electrons can tunnel through the P-N junction mainly because
1.impurity level is low
2.they have high energy
3.barrier potential is very low
4.depletion layer is extremely thin
55.Most of the transistors are NPN type and not PNP type because
1.NPN transistor gives large voltage gain
2.NPN transistors are more negative than PNP transistors
3.In NPN transistor, the current conduction is by free electrons which are less obiles than holes
7. We can have high conduction is NPN transistors
8. In a transistor
1.Emitter is heavily doped while the collector moderately doped
2.Collector base junction is forward biased
3.Emitter is made wider than collector
9. The input resistance is much larger than outp resistance
10. If the instantaneous current in a ckt is given $I=2 \cos (t+\emptyset)$ amperes, the r.m.s. value of $t$ current is
11. 2 amp
12. $\sqrt{ } 2 \mathrm{amp}$
13. $2 \sqrt{ } 2 \mathrm{amp}$
14. Zero amp
15. In an A.C. ckt, voltage and current are given $\mathrm{V}=100 \sin (100 t)$ volts
$\mathrm{i}=100 \sin \left(10 t+\frac{\pi}{3}\right) \mathrm{mA}$. The power dissipated in the ckt is
16. $10^{4}$ watts 2.10 watts
17. 2.5 watts 4.5 watts
59.A $0.05 \mathrm{H}-\mathrm{F}$ capacitor charges through a resistor and is discharged through a resistor $20 \mathrm{~K} £ 2$. The time constant of the circuit is
1.the same both during charging and discharging
2.larger during charging process
3.larger during discharging process
4.none
60.The basic element of radio communica ${ }^{11}$ system which generates radio waves is
18. micro phone 2 . transmitter
3.transmitting antenna 4 . Loudspeaker
61.The input frequency of a bridge rectifier is 50 its output frequency will be
19. $25 \mathrm{~Hz} \quad 2.50 \mathrm{~Hz} \quad 3.75 \mathrm{~Hz} \quad 4.100 \mathrm{~Hz}$
62.Which of the following voltage is used represent binary ' 1 ' in digital circuits.
1.0 V 2.15 V
20. +5 V
21. 25 V
63.Hexadecimal number system is used as a $s$ hand language for representing
22. decimal number 2 . binary number
3.octal number 4. all the above
64.Logic state 0 in positive logic corresponds to
23. zero voltage $\quad 2$. positive voltage
3.higher voltage level 4 . lower voltage level
65.The o/p of a 2 - input OR gate is 1 when its

1 . both inputs are 12 . both inputs are 0
3.either input is 14 . either input is 0
66.TTL logic family is most popularly used industries because it
1.provides greater operating speed
2.has a good fan in \& fan out
3.has easy interface with other digital circuitry
4.all the above
67.Transformer cores are laminated in order to
1.simplify its construction

2 .minimise eddy current loss
3.reduce cost
4.reduce hysteresis loss
68.The external characteristic of a shunt generator can be obtained directly from its - characteristic

1. internal 2 . open-circuit
2. load-saturation 4. Performance
69.Load saturation characteristic of a d.c. generator gives relation between $1 . V$ and $\mathrm{I}_{\mathrm{a}} 2$. E and $\mathrm{I}_{\mathrm{a}} 3$. $\mathrm{E}_{0}$ and $\mathrm{I}_{\mathrm{f}} 4 . V$ and $\mathrm{If}_{\mathrm{f}}$
70.The voltage built-up process of a d.c. generator is
3. difficult 2 . delayed 3 . cumulative 4 . Infinite
71.The biggest advantage of T-T connection over the V-V connection of 3-phase power transformation is that it provides.
1.a set of balanced voltages under load
2.a true 3 -phase, 4 -wire system
4. a higher ratio of utilization
4.more voltages
72.U.H.F. band covers the range of
5. $0-300 \mathrm{KHz} 2.3-30 \mathrm{MHz}$
6. $300-3000 \mathrm{KHz} \quad$ 4. $300 \mathrm{MHz}-3 \mathrm{GHz}$
73.The ripple factor of a bridge rectifier is
1.0.48
2.0.812
7. 1.11
8. 1.21
9. The higher level language is/are
10. Machine language 2.BASIC 3.Assembly language 4. PASCAL
11. The high level language can be translated into machine language with the help of
12. Assembler 2. Stack pointer
13. Compiler 4. Multiplexer
76.In the emitter characteristic of UJT, the negative resistance portion.
1.lies in the cut-off region
2.continues up to peak point
3.lasts until the valley point is reached
4.does not exist
14. After firing as SCR, the gating pulse is removed. The current in the SCR will
15. remain the same 2 . immediately fall to zero 3 . rise up 4 . None
78.When reverse bias is applied to a junction diode, it
1.increases the potential barrier
16. decreases the potential barrier
3.greatly increases the minority carrier current
4.greatly increases the majority carrier current
79.Transformer cores are laminated in order to
1.simplify its construction

2 .minimise eddy current loss
3.reduce cost
4.reduce hysteresis loss
80. When a $\mathrm{P}-\mathrm{N}$ junction is forward biased
1.only electrons in N-region are injected into P-region
2.only holes in P-region are injected into N -region
3.majority carriers in each region are injected into the other region
4.minority current is reduced to zero

## Answers

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| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| 5.1 | 6.4 | 7.3 | $8.1,3$ | 9.1 | 10.2 | 11.4 | 12.3 | 13.4 | 14.1 | 15.3 | 16.2 | 17.4 | 18.1 | 19.1 | 20.2 |
| 21.2 | 22.1 | 23.4 | 24.1 | 25.1 | 26.3 | 27.1 | 28.3 | 29.1 | 30.4 | 31.2 | 32.4 | 33.3 | 34.2 | 35.1 | 36.4 |
| 37.4 | 38.4 | 39.3 | 40.4 | 41.4 | 42.3 | 43.4 | 44.2 | 45.4 | 46.1 | 47.2 | 48.4 | 49.2 | 50.3 | 51.3 | 52.4 |
| 53.4 | 54.4 | 55.4 | 56.1 | 57.2 | 58.3 | 59.2 | 60.2 | 61.4 | 62.3 | 63.2 | 64.4 | 65.3 | 66.2 | 67.2 | 68.2 |
| 69.4 | 70.3 | 71.2 | 72.4 | 73.1 | $74.2,475.3$ | 76.3 | 77.1 | 78.1 | 79.2 | 80.3 |  |  |  |  |  |

